

MOS FIELD EFFECT TRANSISTOR

NP84N055CLE, NP84N055DLE, NP84N055ELE

SWITCHING

N-CHANNEL POWER MOS FET

INDUSTRIAL USE

DESCRIPTION

These products are N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance
 $R_{DS(on)1} = 7.0 \text{ m}\Omega$ MAX. ($V_{GS} = 10 \text{ V}$, $I_D = 42 \text{ A}$)
 $R_{DS(on)2} = 8.7 \text{ m}\Omega$ MAX. ($V_{GS} = 5 \text{ V}$, $I_D = 42 \text{ A}$)
- ★ • Low C_{iss} : $C_{iss} = 6130 \text{ pF}$ TYP.
- Built-in gate protection diode

ORDERING INFORMATION

PART NUMBER	PACKAGE
NP84N055CLE	TO-220AB(MP-25)
NP84N055DLE	TO-262(MP-25 Fin Cut)
NP84N055ELE	TO-263(MP-25ZJ)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage	V_{DSS}	55	V
Gate to Source Voltage	V_{GSS}	± 20	V
Drain Current (DC) ^{Note1}	$I_{D(DC)}$	± 84	A
Drain Current (Pulse) ^{Note2}	$I_{D(pulse)}$	± 336	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_T	1.8	W
★ Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_T	200	W
★ Single Avalanche Current ^{Note3}	I_{AS}	84 / 55 / 20	A
★ Single Avalanche Energy ^{Note3}	E_{AS}	70 / 302 / 400	mJ
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$

Notes 1. Package Limit = $\pm 75 \text{ A}$

2. $PW \leq 10 \mu\text{s}$, Duty cycle $\leq 1 \%$

3. Starting $T_{ch} = 25^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0 \text{ V}$

THERMAL RESISTANCE

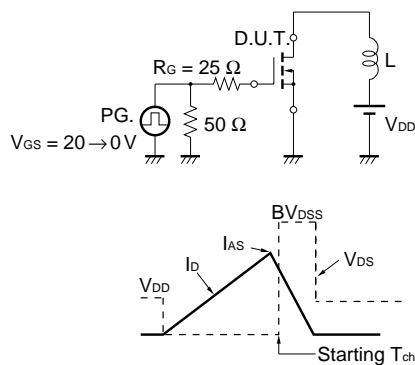
★ Channel to Case	$R_{th(ch-C)}$	0.75	$^\circ\text{C/W}$
★ Channel to Ambient	$R_{th(ch-A)}$	83.3	$^\circ\text{C/W}$

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 Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

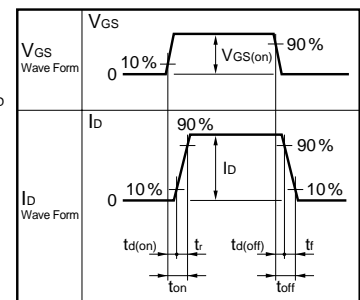
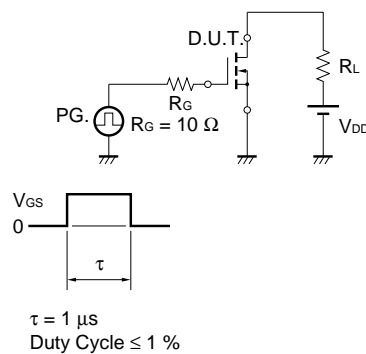
★ ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = 10 V, I _D = 42 A		5.6	7.0	mΩ
	R _{DS(on)2}	V _{GS} = 5 V, I _D = 42 A		6.5	8.7	mΩ
	R _{DS(on)3}	V _{GS} = 4.5 V, I _D = 42 A		7.0	9.4	mΩ
Gate to Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 10 V, I _D = 42 A	29	58		S
Drain Leakage Current	I _{DSS}	V _{DS} = 55 V, V _{GS} = 0 V			10	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Input Capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		6130	9200	pF
Output Capacitance	C _{oss}			710	1070	pF
Reverse Transfer Capacitance	C _{rss}			350	630	pF
Turn-on Delay Time	t _{d(on)}	I _D = 42 A, V _{GS(on)} = 10 V, V _{DD} = 28 V, R _G = 10 Ω		110	240	ns
Rise Time	t _r			1490	3730	ns
Turn-off Delay Time	t _{d(off)}			320	630	ns
Fall Time	t _f			400	990	ns
Total Gate Charge 1	Q _{G1}	I _D = 84 A, V _{DD} = 44 V, V _{GS} = 10 V		120	180	nC
Total Gate Charge 2	Q _{G2}	I _D = 84 A, V _{DD} = 44 V, V _{GS} = 5 V		65	98	nC
Gate to Source Charge	Q _{GS}			18		nC
Gate to Drain Charge	Q _{GD}			33		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 84 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	t _{rr}	I _F = 84 A, V _{GS} = 0 V, di/dt = 100 A/μs		49		ns
Reverse Recovery Charge	Q _{rr}			78		nC

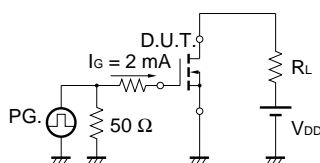
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

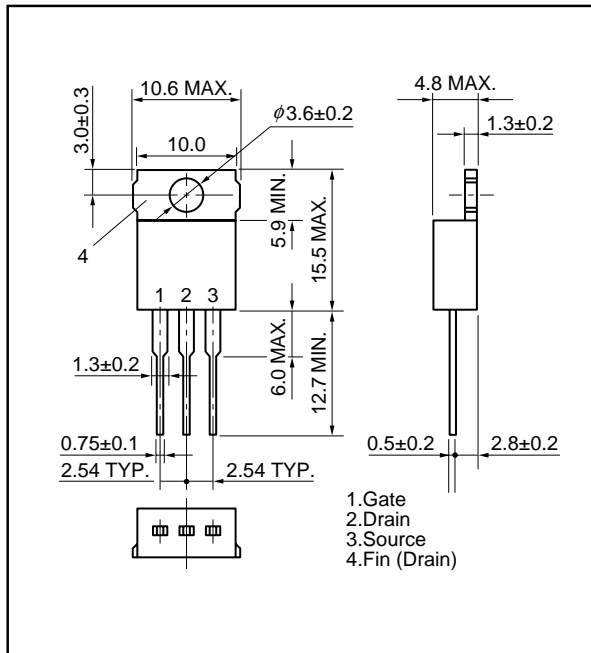


TEST CIRCUIT 3 GATE CHARGE

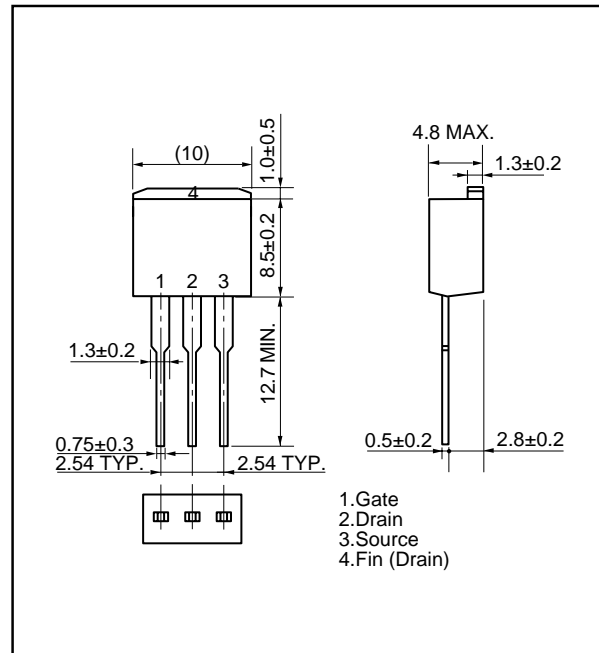


PACKAGE DRAWINGS (Unit: mm)

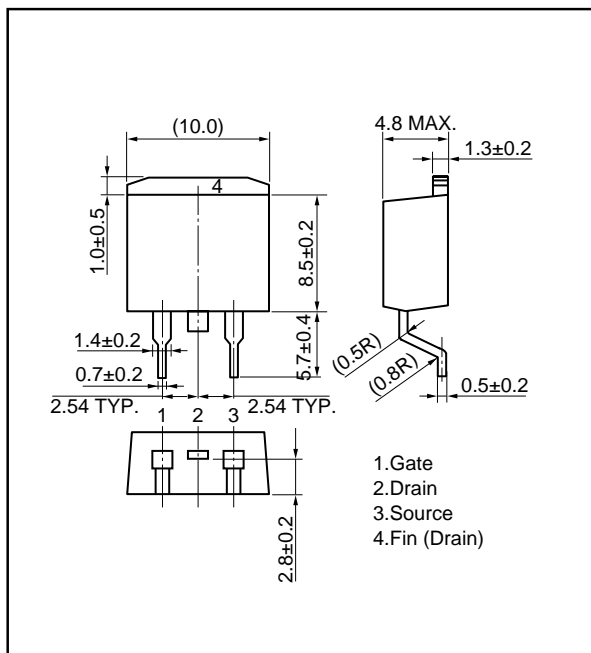
1) TO-220AB (MP-25)



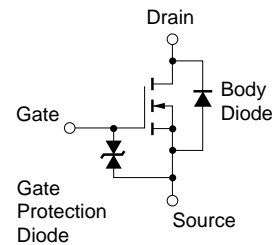
2) TO-262 (MP-25 Fin Cut)



3) TO-263 (MP-25ZJ)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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 - Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
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